IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Accompanying Continuation Application under 37 CFR 1.53:

Prior Application:

K. MOCHIZUKI et al

Serial No. 10/120,505 Filed: April 12, 2002 Group Art Unit: 2813 Examiner: T. Nguyen

For: SEMICONDUCTOR DEVICE AND POWER AMPLIFIER USING THE SAME

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents Alexandria, VA 22314

Sir:

In accordance with the duty of disclosure, the Applicants inform the Examiner of the documents cited during prosecution of the parent application, USSN 10/120,505.

The above-referenced patent application is a divisional application of U.S. Serial No. 10/120,505, filed April 12, 2002, from which priority is claimed under 35 USC §120.

The Applicants request the Examiner to initial and return a copy of the attached PTO-1449 form as an indication that the references have been considered.

Respectfully submitted,

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Date: January 5, 2004

FORM PTO-1449 (REV. 7-80)			U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. SERIAL NO. NIT-337-02		NO.		
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U.S. PATENT DOCUMENTS									
* EXAMINER INITIAL		DOCUMENT	DATE		NAME	CLASS	SUBCLASS	FILING (If Appr	
	AA	5,449,930	09/1995	Zhou, Guo-Gang	j				
	├ ──	5,512,496	04/1996	Chau et al					
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FOREIGN PATENT DOCUMENTS									
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)									
	AR	"Heterojunction bipolar transistors of InGaAs system for microwave power amplifier", OYO-BUTURI, Vol. 66, No. 2, (1997), pp. 156-160.							
		Journal of Vacuum Science and Technology, Vol. 18, No. 2, 2000, pp. 761-764.							
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	AT								
EXAMINER				Di	ATE CONSIDERED				
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with									
next communication to applicant.									